

PATENT APPLICATION
Sheet 1 of 1

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

10031180-1

SERIAL NO.

10/692,772

APPLICANT

Laura Wills Mirkarimi et al.

FILING DATE

Oct. 24, 2003

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | * | DOCUMENT NUMBER | DATE | NAME |
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FOREIGN PATENT DOCUMENTS

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

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| LV | | Grover, Rohit, "Process Development of Methane-Hydrogen-Argon-Based Deep Dry Etching of InP High Aspect-Ratio Structures with Vertical Facet-Quality Sidewalls", Journal of Vacuum Science Technology, B 19(5), Sep/Oct 2001, pp. 1694-1698. |
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EXAMINER

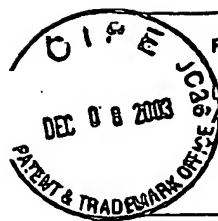
LAN VINH

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5/31/05

* Copies of the references are not enclosed pursuant to 37 CFR 1.98(d). (See accompanying IDS)

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|---------------------|---|-----------------|----------|-------------------------------|
| LV | | 5,624,529 | 04/29/97 | Randy J. Shul et al. |
| LV | | 5,338,394 | 08/16/94 | Mohammed A. Fathimulla et al. |
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

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| LV | | Chen, Hsin-Yi et al., "Inductively Coupled Plasma Etching of InP using CH ₄ /H ₂ and CH ₄ /H ₂ /N ₂ ", Journal of Vacuum Science Technology, B 20(1), Jan/Feb 2002, pp. 47-52. |
| LV | | Hur, Katerina Y., et al., "Reactive Ion Etching of InP Via Holes", Journal of Vacuum Science Technology, B 12(3), May/Jun 1994, pp. 1410-1412. |
| LV | | Feupier, Y. et al., "Influence of the Gas Mixture on the Reactive Ion Etching of InP in CH ₄ -H ₂ Plasmas, Journal of Vacuum Science Technology, B 15(5), Sep/Oct 1997, pp. 1733-1740. |

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